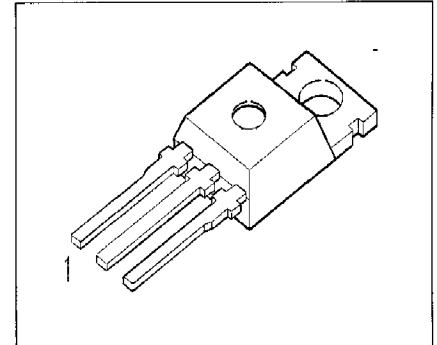


BUZ 10

SIPMOS® Power Transistor

- N channel
- Enhancement mode
- Avalanche-rated

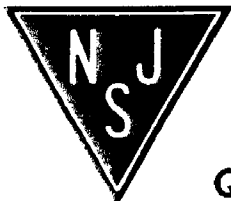


Pin 1	Pin 2	Pin 3
G	D	S

Type	V _{DS}	I _D	R _{DS(on)}	Package
BUZ 10	50 V	23 A	0.07 Ω	TO-220 AB

Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current <i>T_C</i> = 26 °C	I _D	23	A
Pulsed drain current <i>T_C</i> = 25 °C	I _{Dpuls}	92	
Avalanche current, limited by <i>T_{jmax}</i>	I _{AR}	23	
Avalanche energy, periodic limited by <i>T_{jmax}</i>	E _{AR}	1.3	mJ
Avalanche energy, single pulse I _D = 23 A, V _{DD} = 25 V, R _{GS} = 25 Ω L = 15.1 μH, <i>T_j</i> = 25 °C	E _{AS}	8	
Gate source voltage	V _{GS}	± 20	V
Power dissipation <i>T_C</i> = 25 °C	P _{tot}	75	W
Operating temperature	<i>T_j</i>	-55 ... + 150	°C
Storage temperature	<i>T_{stg}</i>	-55 ... + 150	
Thermal resistance, chip case	R _{thJC}	≤ 1.67	K/W
Thermal resistance, chip to ambient	R _{thJA}	≤ 75	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	



Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Drain- source breakdown voltage $V_{GS} = 0\text{ V}, I_D = 0.25\text{ mA}, T_j = 25^\circ\text{C}$	$V_{(BR)DSS}$	50	-	-	V
Gate threshold voltage $V_{GS} = V_{DS}, I_D = 1\text{ mA}$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, T_j = 25^\circ\text{C}$ $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, T_j = 125^\circ\text{C}$	I_{DSS}	-	0.1 10	1 100	μA
Gate-source leakage current $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	-	10	100	nA
Drain-Source on-resistance $V_{GS} = 10\text{ V}, I_D = 14\text{ A}$	$R_{DS(on)}$	-	0.05	0.07	Ω

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 14 \text{ A}$	g_{fs}	7	13	-	S
Input capacitance $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	C_{iss}	-	650	820	pF
Output capacitance $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	C_{oss}	-	300	450	
Reverse transfer capacitance $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	C_{rss}	-	110	170	
Turn-on delay time $V_{DD} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_{d(on)}$	-	20	35	ns
Rise time $V_{DD} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	t_r	-	40	65	
Turn-off delay time $V_{DD} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_{d(off)}$	-	80	110	
Fall time $V_{DD} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	t_f	-	60	75	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current $T_C = 25^\circ\text{C}$	I_S	-	-	23	A
Inverse diode direct current, pulsed $T_C = 25^\circ\text{C}$	I_{SM}	-	-	92	
Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = 46\text{ A}$	V_{SD}	-	1.5	1.9	V
Reverse recovery time $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	60	-	ns
Reverse recovery charge $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	0.1	-	μC